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Applicant: Toru YAMADA et al.

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Docket No: SUG-193-PCT

Customer No: 28892

For: Vapor Phase Growth Apparatus and Method of Fabricating Epitaxial Wafer

INFORMATION DISCLOSURE STATEMENT - PTO FORM 1449

FOREIGN PATENT DOCUMENTS				
Examiner Initials*	Foreign Patent Document Number	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T**
/F.H./	JP 2002-231641 w/ English Abstract	Shinetsu Handotai KK Nagano Electronics Ind	08-16-2002	
/F.H./	JP 2002-198316 w/ English Abstract	Shinetsu Handotai KK Nagano Electronics Ind	07-12-2002	
/F.H./	JP 2001-44125 w/ English Abstract	Applied Materials Inc	02-16-2001	
/F.H./	JP 2000-331939 w/ English Abstract	Applied Materials Inc	11-30-2000	
/F.H./	JP 7-193015	Applied Materials Inc	07-28-1995	X
/F.H./	EP 0 637 058 A1	Applied Materials Inc	02-01-1995	
/F.H./	EP 0 637 058 B1	Applied Materials Inc	02-01-1995	

Examiner Signature	/Felisa Hiteshew/	Date Considered	09/08/2008
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*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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